ON Semiconductor

Is Now

Onsemi

To learn more about onsemi[™], please visit our website at <u>www.onsemi.com</u>

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product factures, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and asfety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or by customer's technical experts. onsemi products and actal performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiari

Dual Operational Amplifier, 7 MHz Bandwidth with Shutdown

NCS20282

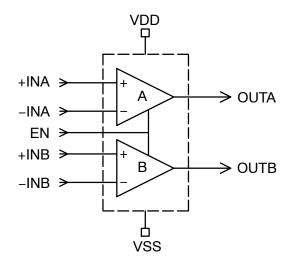
The NCS20282 high precision op amp features a wide bandwidth along with shutdown. These amplifiers provide low bias current useful for transimpedance applications. The wide bandwidth eases the design of active filters. The NCS20282 is specified for operation from -40°C to +125°C.

Features

- High Bandwidth: 7 MHz typical
- Low Bias Current: 50 pA typical
- Rail-to-Rail Input/Output
- Shutdown Current: 1 µA max
- Offset Voltage: 1.5 mV max
- Offset Drift: 10 µV/°C max
- Supply Voltage: 2.5 V to 5.5 V
- These Devices are Pb-free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Transducer Applications
- Sensor Conditioning
- Medical Instrumentation
- Impedance Sensing





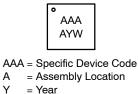
ON Semiconductor®

www.onsemi.com



WLCSP9 CASE 567YD

MARKING DIAGRAM



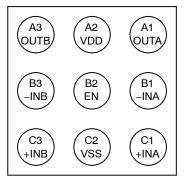
= Work Week W

Α

Υ

(Note: Microdot may be in either location)

PIN CONNECTIONS



Package Bottom View (Bump Up)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 9 of this data sheet.

This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.

Table 1. ABSOLUTE MAXIMUM RATINGS Over operating free-air temperature, unless otherwise stated.

Parameter	Rating	Unit V	
Supply Voltage (VDD- VSS)	7		
INPUT AND OUTPUT PINS	·		
Input Voltage (Note 1)	$(V_{SS}-0.5)$ to 7	V	
Input Current (Note 1)	±5	mA	
Output Pin Voltage, Disabled	7	V	
Output Short Circuit Current (Note 2)	Continuous		
TEMPERATURE			
Operating Temperature	-40 to +125	°C	
Storage Temperature	-65 to +150	°C	
Junction Temperature	+150	°C	
ESD RATINGS (Note 3)			
Human Body Model (HBM)	2000	V	
Charged Device Model (CDM)	1000	V	
OTHER RATINGS			
Latch-up Current (Note 4)	100		
MSL	Level 1		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The input voltage at any pin may exceed the voltage shown if the current at that pin is limited to 5 mA.

2. Short-circuit to ground.

3. This device series incorporates ESD protection and is tested by the following methods:

ESD Human Body Model tested per JEDEC standard JS-001-2017

ESD Charged Device Model tested per JEDEC standard JS-002-2014

4. Latch-up Current tested per JEDEC standard: JESD78

Table 2. THERMAL INFORMATION

Parameter	Symbol	Cu Area mm ²	1.0 oz	2.0 oz	Unit
Thermal Resistance	Θ_{JA}	10	301	263	°C/W
Junction to Ambient		25	263	230	
		40	246	215	
		80	229	204	
		140	220	196	
		250	211	188	
		350	206	183	
		500	200	179	
		650	197	175	1
		800	194	173	

NOTE: Four layer JSEC JESD51-7

Table 3. OPERATING CONDITIONS

Parameter	Symbol	Range	Units
Supply Voltage (V _{DD} – V _{SS})	V _S	2.5 to 5.5	V
Specified Operating Temperature Range	T _A	-40 to +125	°C
Input Common Mode Voltage Range	V _{CM}	V_{SS} to V_{DD}	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 4. ELECTRICAL CHARACTERISTICS: $V_S = 2.5 V$ to 5.5 VAt $T_A = +25^{\circ}C$, $R_L = 10 k\Omega$, $V_{CM} = V_{OUT}$ = midsupply, Enable input connected to V_{DD} , unless otherwise noted. **Boldface** limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to $+125^{\circ}C$, guaranteed by characterization and/or design

Parameter		Symbol	Condit	tions	Min	Тур	Max	Units
INPUT CHARACTERISTIC	S		-			-		
Offset Voltage		V _{OS}				300	1500	μV
Offset Voltage Drift vs Temp		$\Delta V_{OS} / \Delta T$				2	10	μV/°C
Input Bias Current (Note 5)		I _{IB}				50	800	pА
Input Offset Current		I _{OS}				10		pА
Input Common-Mode Voltag	ge Range	V _{CM}				V_{SS} to V_{DD}		V
Common Mode Rejection R	atio	CMRR	$V_{CM} = -0.1 V to$	o (V _{DD} +0.1V)	66	86		dB
Input Resistance		R _{IN}	Differe	ential		10		GΩ
			Commor	n Mode		10		
Input Capacitance		C _{IN}	Differe	ential		2		pF
			Commor	n Mode		5		
OUTPUT CHARACTERIST	ICS							
Open Loop Voltage Gain		A _{VOL}	$0.4 V \le V_{OUT} \le$	$V_{DD} - 0.4 V$	96	116		dB
Closed Loop Output Impeda	ance	Z _{OUT_CL}	See Fig	ure 23		See Figure 23		Ω
Output Voltage High, Refere	enced to V _{DD}	V _{OH}				V _{DD} -3	V _{DD} -10	mV
Output Voltage Low, Refere	nced to V _{SS}	V _{OL}				V _{SS} +6	V _{SS} +10	mV
Short Circuit Current (Note	5)	I _{SC}	Sinking C	Current		10	15	mA
			Sourcing	Current		10	15	1
Capacitive Load Drive (Note	e 5)	CL				100	300	pF
DYNAMIC PERFORMANCI	E							
Gain Bandwidth Product (No	ote 5)	GBW	$\label{eq:VS} \begin{array}{l} V_S = 3 \ V; \\ R_L = 10 \ k\Omega, \ C_L = 100 \ pF \end{array}$		5.4	7		MHz
Gain Margin		A _M	C _L = 100 pF			50		dB
Phase Margin		Ψ_{M}	C _L = 10	00 pF		55		0
Slew Rate		SR	A _V = +1			5		V/µs
Overload Recovery Time		t _{OR}	V _{IN} X A	/ > V _S		1		μs
NOISE PERFORMANCE								
Voltage Noise Density		e _N	f _{IN} = 10 kHz			20		nV/√Hz
Current Noise Density		i _N	f _{IN} = 1			300		fA/√Hz
POWER SUPPLY			-					
Power Supply Rejection Ratio		PSRR			90	120		dB
Shutdown Enable Time (Notes 5, 6)		t _{ON}				30	50	μs
Shutdown Disable Time (Note 6)		t _{OFF}				30		μs
Shutdown Leakage Input Output			V _{IN} = V _S +	400 mV			500	nA
		1	V _{OUT} = V _S +1 V				500	1
Enable Input Threshold Voltage		V _{th(EN)}	Operating		1.3			V
			Disabled				0.5	1
Enable Input Leakage Current		age Current I _{Enable}		Enable = + 5.0 V		1.1		μA
			Enable = V_{SS}			1.1		
Quiescent Current I _Q		Ι _Q	Per Channel	Quiescent		850	1300	μA
		1	No load	Shutdown		0.3	1	1

Guaranteed by design and/or characterization
Shutdown Disable Time (t_{OFF}) and Enable Time (t_{ON}) are defined as the time between the 50% point of the signal applied to the EN pin and the point at which the output voltage reaches the 10% (disable) or 90% (enable) level.
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

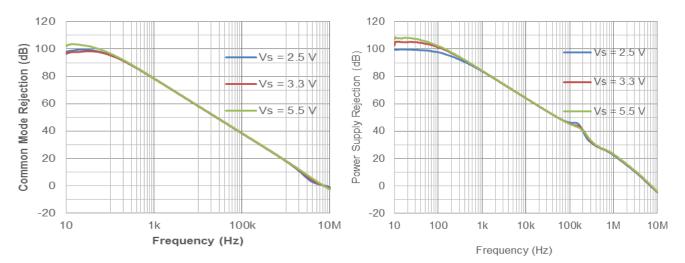
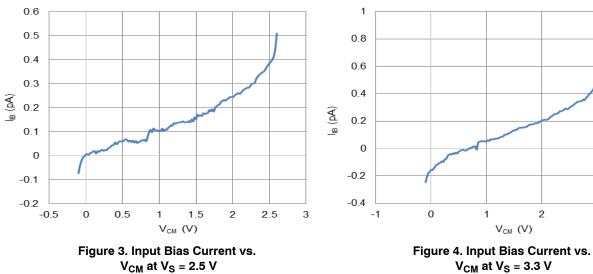


Figure 1. CMRR vs. Frequency

Figure 2. PSRR vs. Frequency

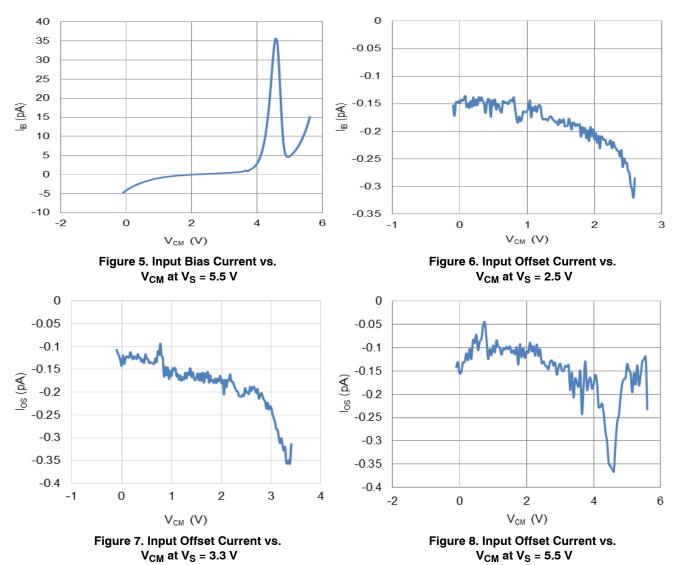


 V_{CM} at $V_S = 3.3 V$

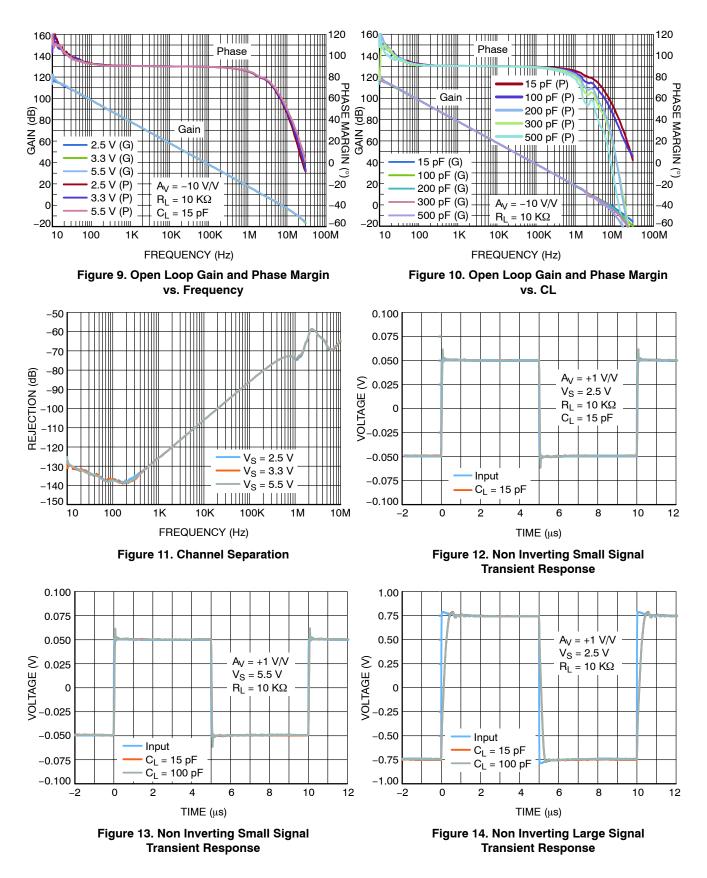
3

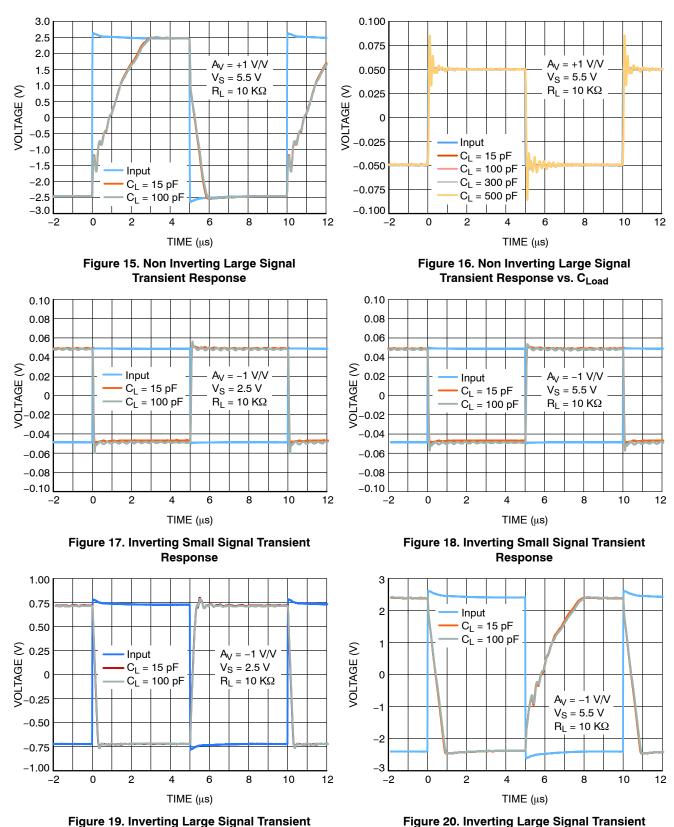
4





TYPICAL CHARACTERISTICS



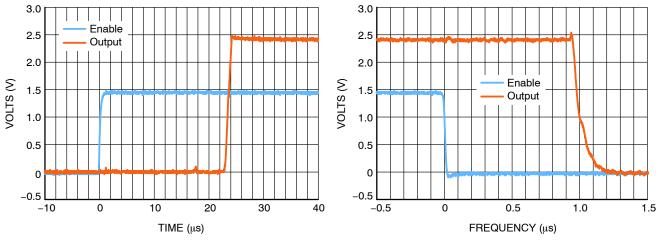


TYPICAL CHARACTERISTICS

www.onsemi.com

Response

Response



TYPICAL CHARACTERISTICS





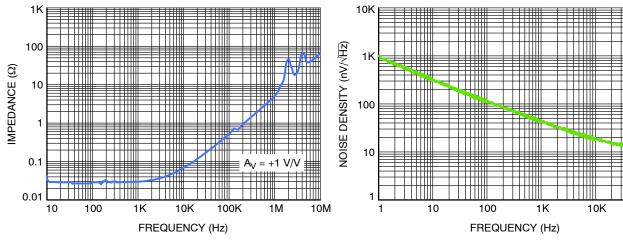


Figure 23. Closed Loop Output Impedance

Figure 24. Voltage Noise Density vs. Frequency

100K

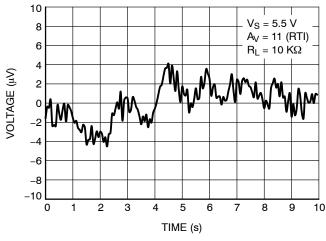


Figure 25. 0.1 Hz to 10 Hz Noise

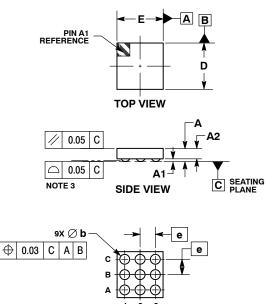
DEVICE ORDERING INFORMATION

Device	Marking	Bump Type	Case Outline	Package	Shipping [†]
NCS20282FCTTAG	AAA	Sn Plate	567UW	WLCSP-9 (Pb-Free)	5000 / Tape & Reel
NCS20282FCSTAG* (In Development)	AAA	SAC 405	567YD	WLCSP-9 (Pb-Free)	5000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

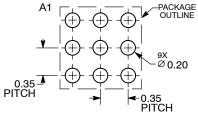
WLCSP9, 1.02x1.02x0.33 CASE 567UW **ISSUE A**



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE SOLDER BALLS.

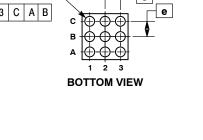
	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α			0.33	
A1	0.04	0.06	0.08	
A2	0.23 REF			
b	0.180	0.200	0.220	
D	0.99	1.02	1.05	
Е	0.99	1.02	1.05	
e	0.35 BSC			

RECOMMENDED SOLDERING FOOTPRINT*



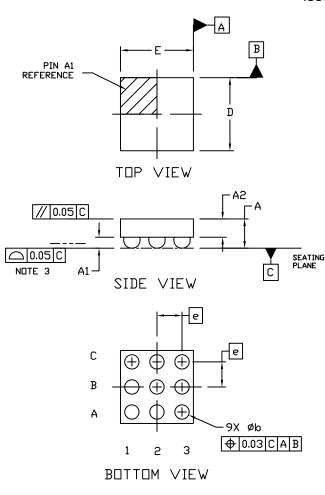
DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



PACKAGE DIMENSIONS

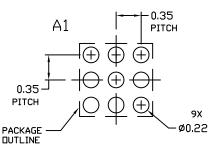
WLCSP9, 1.02x1.02x0.441 CASE 567YD ISSUE O



NDTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE SOLDER BALLS.

	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
Α			0.441	
A1	0.133	0.153	0.173	
A2	0.255 REF			
b	0.183	0.203	0.223	
D	0.99	1.02	1.05	
E	0.99	1.02	1.05	
e	0.35 BSC			



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the UN Semiconductor Soldering and Mounting Techniques Reference Manual, SULDERRM/D.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make charges without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor hands is against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury o

ж

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

TECHNICAL SUPPORT

ON Semiconductor Website: www.onsemi.com

North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910 Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative